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December 2013

FQP6N80C / FQPF6N80C

N-Channel QFET® MOSFET

800 V, 5.5 A, 2.5 Ω

Description

This N-Channel enhancement mode power MOSFET is • 5.5 A, 800 V, $R_{DS(on)}$ = 2.5 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 21 nC) resistance, and to provide superior switching performance

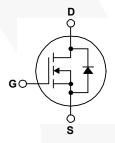
• Low Crss (Typ. 8 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 2.75 A$







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP6N80C	FQPF6N80C / FQPF6N80CT	Unit
V _{DSS}	Drain-Source Voltage		800		V
I _D	Drain Current - Continuous (T _C = 25°C)		5.5	5.5 *	Α
	- Continuous (T _C = 100°C)	F	3.2	3.2 *	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	22	22 *	Α
V _{GSS}	Gate-Source Voltage		± 30		V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	680		mJ
I _{AR}	Avalanche Current	(Note 1)	5.5		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		15.8		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P_{D}	Power Dissipation (T _C = 25°C)		158	51	W
	- Derate above 25°C		1.27	0.41	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300		°C	

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP6N80C	FQPF6N80C / FQPF6N80CT	Unit
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.79	2.45	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP6N80C	FQP6N80C	TO-220	Tube	N/A	N/A	50 units
FQPF6N80C	FQPF6N80C	TO-220F	Tube	N/A	N/A	50 units
FQPF6N80CT	FQPF6N80CT	TO-220F	Tube	N/A	N/A	50 units

Flootrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.97		V/°C
I _{DSS} Zero Gate Vo	7 0 1 1/1 5 1 0 1	V _{DS} = 800 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 640 V, T _C = 125°C			100	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.75 A		2.1	2.5	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 2.75 A		5.4		S
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		1010	1310	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		90	115	pF
C _{rss}	Reverse Transfer Capacitance			8	11	рF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 5.5 A,		26	60	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		65	140	ns
$t_{d(off)}$	Turn-Off Delay Time			47	105	ns
t _f	Turn-Off Fall Time	(Note 4)		44	90	ns
Qg	Total Gate Charge	V _{DS} = 640 V, I _D = 5.5 A,	/	21	30	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		6		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		9		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				5.5	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current			/	22	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 5.5 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 5.5 A,		615		ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		5.4	\	μС

- Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 42 mH, I_{AS} = 5.5 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} ≤ 5.5 A, di/dt ≤ 200 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

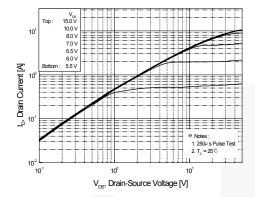


Figure 1. On-Region Characteristics

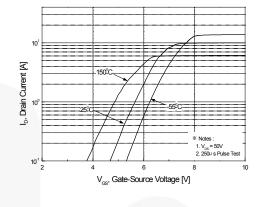


Figure 2. Transfer Characteristics

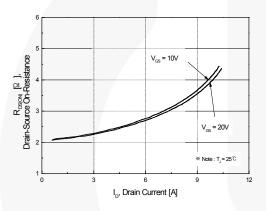


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

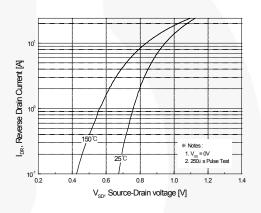


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

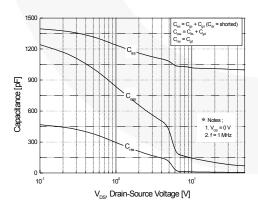


Figure 5. Capacitance Characteristics

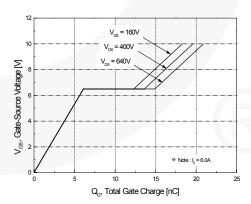


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

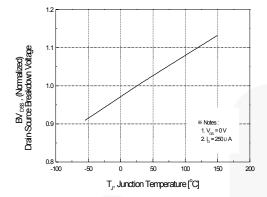


Figure 7. Breakdown Voltage Variation vs Temperature

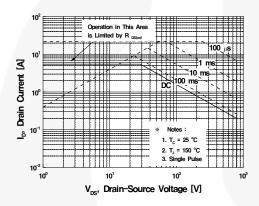


Figure 9-1. Maximum Safe Operating Area for FQP6N80C

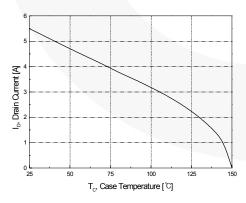


Figure 10. Maximum Drain Current vs Case Temperature

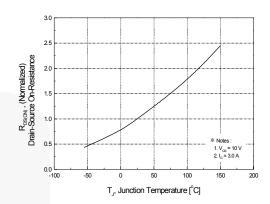


Figure 8. On-Resistance Variation vs Temperature

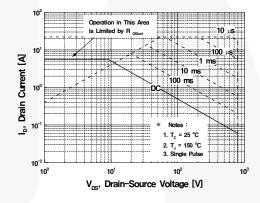


Figure 9-2. Maximum Safe Operating Area for FQPF6N80C

Typical Characteristics (Continued)

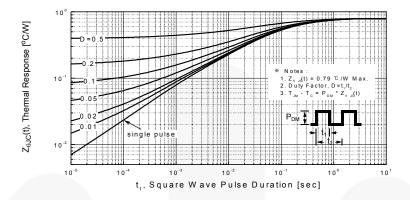


Figure 11-1. Transient Thermal Response Curve for FQP6N80C

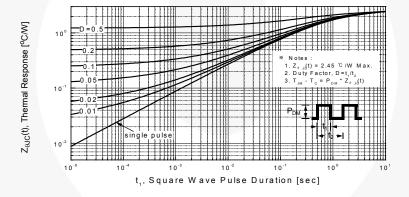


Figure 11-2. Transient Thermal Response Curve for FQPF6N80C

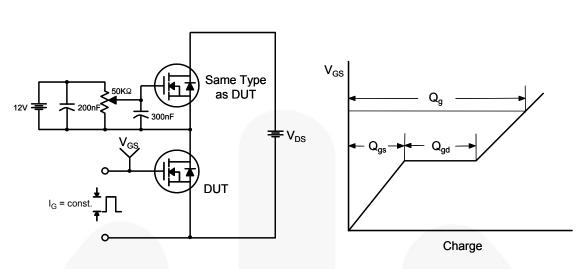


Figure 12. Gate Charge Test Circuit & Waveform

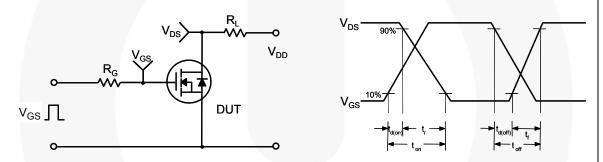


Figure 13. Resistive Switching Test Circuit & Waveforms

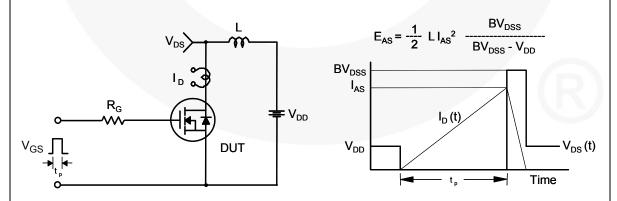
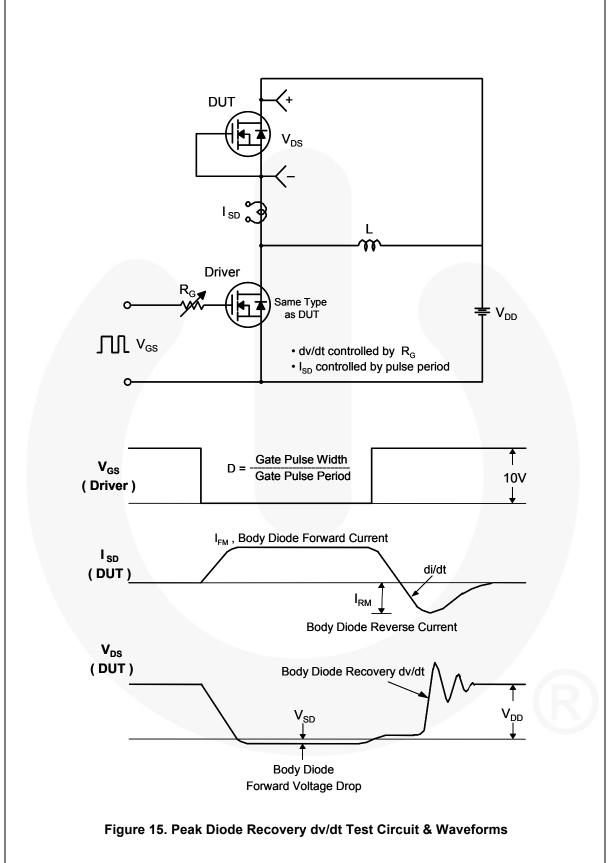


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

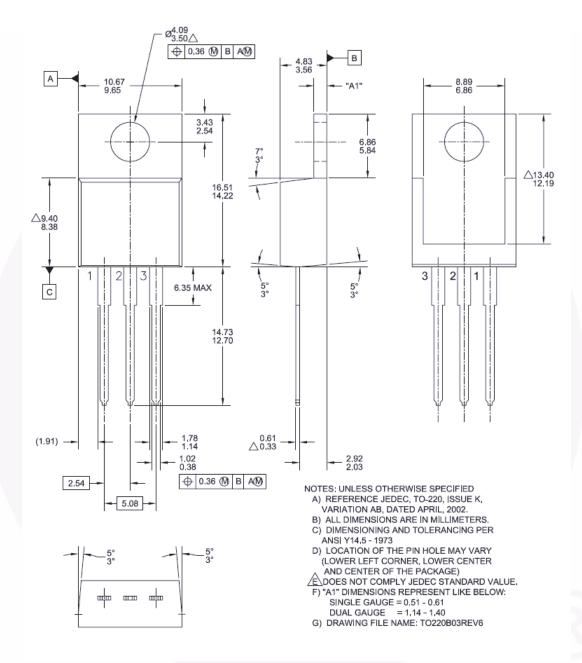


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

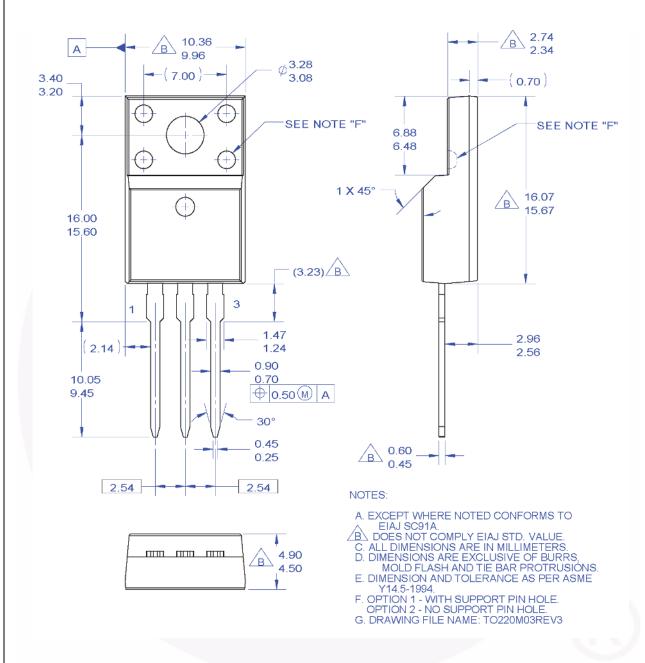


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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